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SEMICONDUCTOR

November 2013

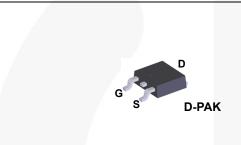
FQD13N10 N-Channel QFET[®] MOSFET 100 V, 10 A, 180 mΩ

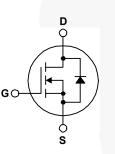
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce . Low Gate Charge (Typ. 12 nC) on-state resistance, and to provide superior switching • Low Crss (Typ. 20 pF) performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, • 100% Avalanche Tested audio amplifier, DC motor control, and variable switching power applications.

Features

- 10 A, 100 V, $R_{DS(on)}$ = 180 m Ω (Max.) @ V_{GS} = 10 V, I_D = 5 A





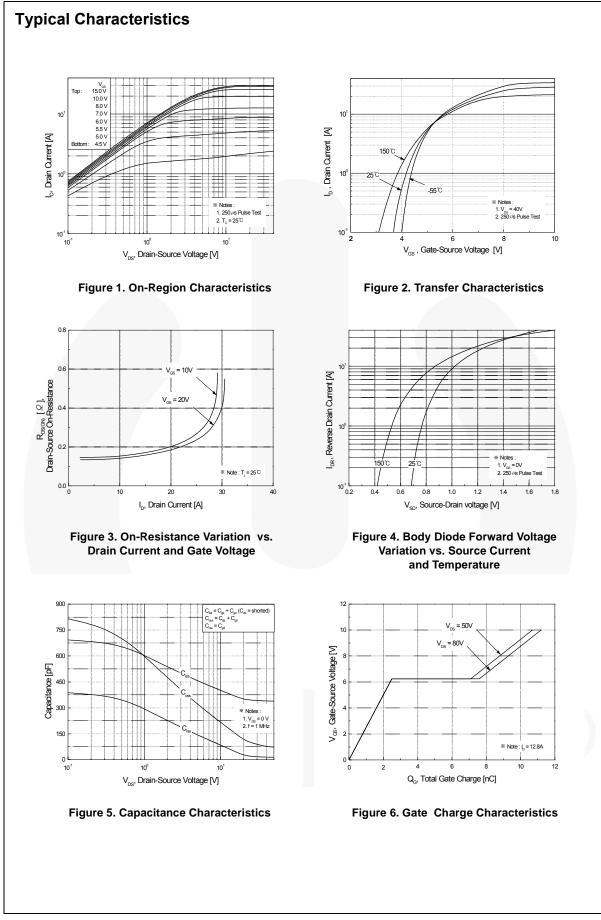
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

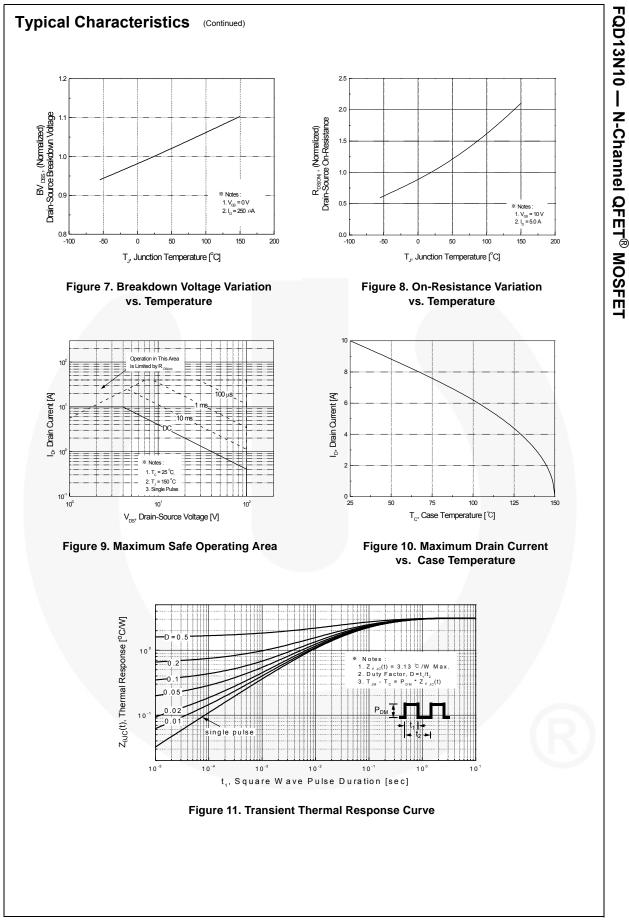
Symbol	Parameter	FQD13N10TM	Unit
V _{DSS}	Drain-Source Voltage	100	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)	10	A
	- Continuous (T _C = 100°C)	6.3	A
I _{DM}	Drain Current - Pulsed (N	ote 1) 40	А
V _{GSS}	Gate-Source Voltage	± 25	V
E _{AS}	Single Pulsed Avalanche Energy (N	ote 2) 95	mJ
I _{AR}	Avalanche Current (N	ote 1) 10	A
E _{AR}	Repetitive Avalanche Energy (N	ote 1) 4.0	mJ
dv/dt	Peak Diode Recovery dv/dt (N	ote 3) 6.0	V/ns
P _D	Power Dissipation ($T_A = 25^{\circ}C$) *	= 25°C) * 2.5	
	Power Dissipation (T _C = 25°C)	40	W
	- Derate above 25°C	0.32	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
ΤL	Maximum lead temperature for soldering, .1/8" from case for 5 seconds	300	°C

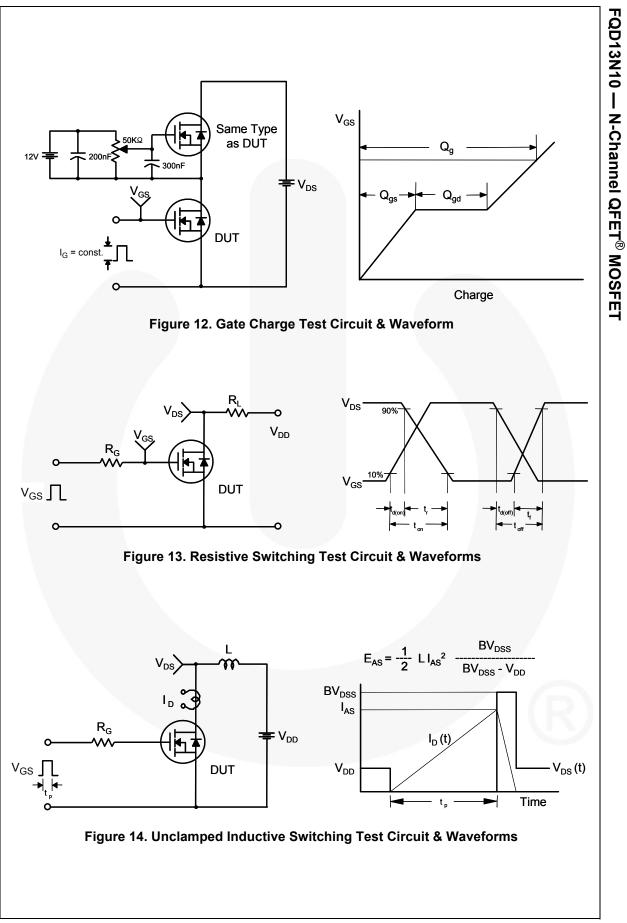
Thermal Characteristics

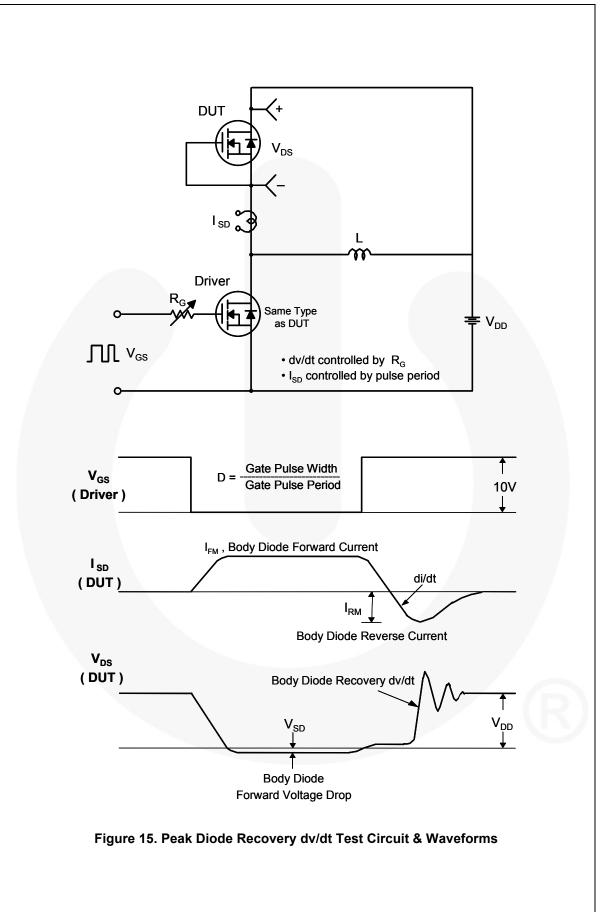
Symbol	Parameter	FQD13N10TM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	3.13	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

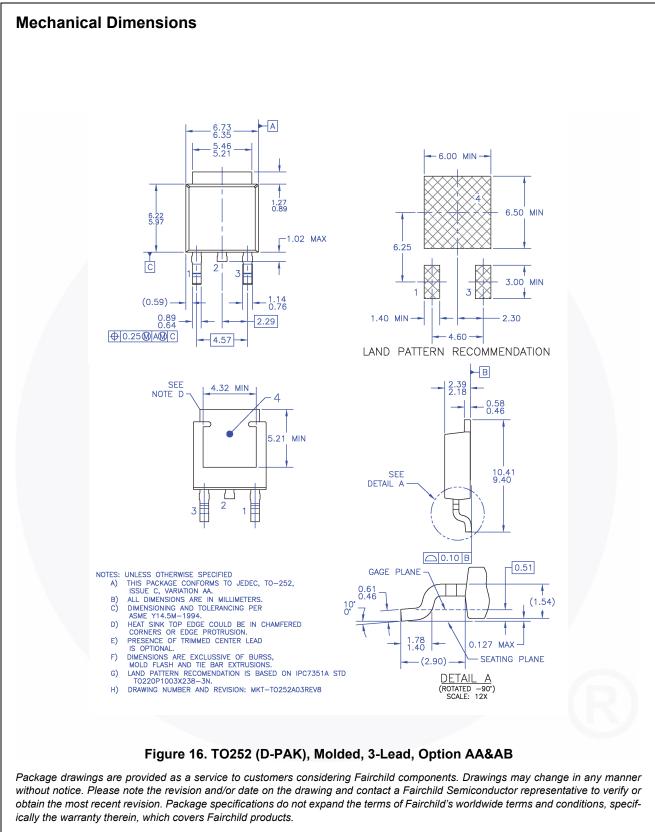
lectric Symbol Off Cha SV _{DSS} ABV _{DSS}		FQD13N10		\aye	Fackin	kage Packing Method Reel		Size	Tape W	lath	Quantity
Symbol Off Cha ^{3V_{DSS} ABV_{DSS}}	cal Chai		-				330	mm	16 mm		2500 units
Symbol Off Cha ^{3V_{DSS} ABV_{DSS}}	cal Cha										
Dff Cha BV _{DSS} ABV _{DSS}		racteristics	T _C = 25°0	C unless oth	herwise noted						
BV _{DSS}		Parameter			Test Co	nditions		Min	Тур	Мах	Unit
BV _{DSS}	aracterist	ics									
ΔBV _{DSS} /ΔTJ	Drain-Source Breakdown Voltage			V _{GS} = 0 V, I _D = 250 μA			100			V	
iΔiJ	Coefficient			I_D = 250 µA, Referenced to 25°C				0.09	0.09	V/°C	
DSS	7			V _{DS} =	V _{DS} = 100 V, V _{GS} = 0 V					1	μA
	Zero Gate	Voltage Drain Curr	rent	V _{DS} =	80 V, T _C =	125°C				10 100	μA
GSSF	Gate-Body	y Leakage Current,	Forward	V _{GS} =	25 V, V _{DS}	= 0 V					nA
GSSR	Gate-Body	y Leakage Current,	Reverse	V _{GS} =	-25 V, V _{DS}	_s = 0 V				-100	nA
	aracteristi			1							-1
/ _{GS(th)}		shold Voltage		V _{DS} =	V _{GS} , I _D = 1	250 µA		2.0		4.0	V
R _{DS(on)}	Static Drai			V _{GS} =	10 V, I _D =	5.0 A			0.142	0.18	Ω
	On-Resista		_	V -	40 V, I _D =	500	_		6.2		S
FS	Forward I	ransconductance	_	VDS -	40 V, I _D -	5.0 A	_		6.3		3
Dvnami	ic Charac	teristics									
Ciss	Input Capa		_	V -	25 \/ \/	- 0.1/			345	450	pF
Coss	· · ·	Output Capacitance			25 V, V _{GS} мн 7	= 0 V,			100	130	pF
	Reverse Transfer Capacitance			f = 1.0 MHz							
2 _{rss}	ILEVEISE I		C I						20	25	pF
Prss	Treverse I	1							20	25	pF
		acteristics							20	25	pF
Switchi		acteristics		Voo =	50 V In =	12.8 Δ			20 5	25 20	pF ns
Switchi	ing Chara	acteristics Delay Time			50 V, I _D =	12.8 A,					
Switchi d(on) r	ing Chara Turn-On D	acteristics Delay Time Rise Time		V _{DD} = R _G = 2	5				5	20	ns
Switchi d(on) r d(off) f	ing Chara Turn-On D Turn-On R	acteristics Delay Time Rise Time Delay Time			5		(Note 4)		5 55	20 120	ns
Switchi d(on) r d(off) f	ing Chara Turn-On D Turn-On R Turn-Off D	acteristics Delay Time Rise Time Delay Time Call Time		R _G = 2	5	((Note 4)		5 55 20	20 120 50	ns ns ns
C _{rss} Switchi d(on) r d(off) f Q _g Q _{gs}	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate	acteristics Delay Time Rise Time Delay Time Call Time		R _G = 2	25 Ω 80 V, I _D =	((Note 4)		5 55 20 25	20 120 50 60	ns ns ns ns
Switchi d(on) r d(off) f Q _g	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate	acteristics Delay Time Rise Time Delay Time Call Time Charge Tree Charge		R _G = 2	25 Ω 80 V, I _D =	(12.8 A,	(Note 4)		5 55 20 25 12	20 120 50 60	ns ns ns ns nC
Switchi d(on) r d(off) f λ_g λ_{gs} λ_{gd}	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain	acteristics Delay Time Rise Time Delay Time Call Time Charge Charge n Charge		R _G = 2 V _{DS} = V _{GS} =	25 Ω 80 V, I _D = 10 V	(12.8 A, (5 55 20 25 12 2.5	20 120 50 60 16 	ns ns ns ns nC nC
Switchi d(on) r d(off) f Qg Qgs Qgd Drain-S	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain	Acteristics Delay Time Rise Time Delay Time Call Time Charge rce Charge n Charge ode Character	istics a	$R_G = 2$ $V_{DS} =$ $V_{GS} =$	25 Ω 80 V, I _D = 10 V kimum F	12.8 A, () Ratings			5 55 20 25 12 2.5	20 120 50 60 16 	ns ns ns ns nC nC
Switchi d(on) r d(off) f 2g 2gs 2gd Drain-S s	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Dia	Acteristics Delay Time Rise Time Delay Time all Time Charge Charge n Charge ode Character Continuous Drain-S	istics al	$R_G = 2$ $V_{DS} =$ $V_{GS} =$ nd Max	25 Ω 80 V, $I_D =$ 10 V kimum F vard Curre	12.8 A, () Ratings			5 55 20 25 12 2.5	20 120 50 60 16 10	ns ns ns nC nC nC A
Switchi d(on) r d(off) f Q _g Q _{gs} Q _{gd} Drain-S s SM	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Dia Maximum Maximum	acteristics Delay Time Rise Time Delay Time a Charge Charge Tree Charge n Charge Ode Characteri Continuous Drain-S Pulsed Drain-Source	istics ar Source Dic ce Diode F	R _G = 2 V _{DS} = V _{GS} = Md Max	$P_{25 \Omega}$ 80 V, I _D = 10 V kimum F vard Current	(12.8 A, (Ratings nt		 	5 55 20 25 12 2.5 5.1	20 120 50 60 16 10 40	ns ns ns nC nC nC A A
Switchi	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Did Maximum Maximum Drain-Sou	acteristics Delay Time Rise Time Delay Time Gall Time Charge Charge Charge Charge Ode Characteri Continuous Drain-S Pulsed Drain-Source rce Diode Forward	istics ar Source Dic ce Diode F	$R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $M_{GS} =$ $M_{GS} =$ $M_{GS} =$ $M_{GS} =$ $M_{GS} =$	$80 \text{ V, } \text{I}_{\text{D}} =$ $80 \text{ V, } \text{I}_{\text{D}} =$ 10 V $\frac{\text{kimum F}}{\text{vard Current}}$ $\frac{\text{Current}}{0 \text{ V, } \text{I}_{\text{S}} = 1$	(12.8 A, (Ratings nt 0 A			5 55 20 25 12 2.5 5.1	20 120 50 60 16 10	ns ns ns nC nC nC A A A V
Switchi d(on) r d(off) f Ω_g Ω_{gs} Ω_{gd}	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Did Maximum Maximum Drain-Sou Reverse R	acteristics Delay Time Rise Time Delay Time a Charge Charge Tree Charge n Charge Ode Characteri Continuous Drain-S Pulsed Drain-Source	istics ar Source Dic ce Diode F	$R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $V_{GS} =$ $V_{GS} =$ $V_{GS} =$ $V_{GS} =$	$P_{25 \Omega}$ 80 V, I _D = 10 V kimum F vard Current	12.8 A, () Ratings nt 0 A 2.8 A,			5 55 20 25 12 2.5 5.1	20 120 50 60 16 10 40	ns ns ns nC nC nC A A











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FQD13N10 — N-Channel QFET[®] MOSFET



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QD13N10

N-Channel QFET[®] MOSFET

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